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## SiC for Proton Beam Monitor

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Silicon carbide is a new type of semiconductor, and it is widely used in optoelectronic devices, power electronic devices and other fields. Compared to silicon semiconductor, silicon carbide has wider band gap, higher breakdown electric field, higher thermal conductivity and can stand greater irradiation.

We are planning to use silicon carbide device to make a proton beam monitoring system. We will present the SiC PIN sensors performance, and the current progress of the electronics development.

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